



NDD03N80Z-1G Information



For Reference Only

Part Number NDD03N80Z-1G
Manufacturer ON Semiconductor

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 800V 2.9A IPAK

Package TO-251-3 Short Leads, IPak, TO-251AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









NDD03N80Z-1G Specifications

Manufacturer Part Number NDD03N80Z-1G Manufacturer ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-251-3 Short Leads, IPak, TO-251AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 800V Current - Continuous Drain (Id) @ 25°C 2.9A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 50µA Gate Charge (Qg) (Max) @ Vgs 17nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 440F @ 25V Vgs (Max) 440F @ 25V Vgs (Max) 9W FET Feature - Power Dissipation (Max) 96W (Tc) Rds On (Max) @ Id, Vgs 4.5 Ohm @ 1.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-251-3 Short Leads, IPak, TO-251AASeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C2.9A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 50µAGate Charge (Qg) (Max) @ Vgs17nC @ 10VInput Capacitance (Ciss) (Max) @ Vds440pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)96W (Tc)Rds On (Max) @ Id, Vgs4.5 Ohm @ 1.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device Package1-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Manufacturer Part Number	NDD03N80Z-1G
Package TO-251-3 Short Leads, IPak, TO-251AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 800V Current - Continuous Drain (Id) @ 25°C 2.9A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 50μA Gate Charge (Qg) (Max) @ Vgs 17nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 440pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 96W (Tc) Rds On (Max) @ Id, Vgs 4.5 Ohm @ 1.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 1-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Manufacturer	ON Semiconductor
PackageTO-251-3 Short Leads, IPak, TO-251AASeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C2.9A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 50μAGate Charge (Qg) (Max) @ Vgs17nC @ 10VInput Capacitance (Ciss) (Max) @ Vds440pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)96W (Tc)Rds On (Max) @ Id, Vgs4.5 Ohm @ 1.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device Package1-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Category	Discrete Semiconductor Products
Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C2.9A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 50μAGate Charge (Qg) (Max) @ Vgs17nC @ 10VInput Capacitance (Ciss) (Max) @ Vds440pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)96W (Tc)Rds On (Max) @ Id, Vgs4.5 Ohm @ 1.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Bount to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature John (J Vgs Mounting Type Through Hole Supplier Device Package Package / Case N-Cannel N-Channel Above 10V 2.9A (Tc) 17nC @ 10V 4.5V @ 50µA 440pF @ 25V 440pF @ 25V 450V 450V 450V Through Hole I-Pak Package / Case	Package	TO-251-3 Short Leads, IPak, TO-251AA
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C2.9A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 50μAGate Charge (Qg) (Max) @ Vgs17nC @ 10VInput Capacitance (Ciss) (Max) @ Vds440pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)96W (Tc)Rds On (Max) @ Id, Vgs4.5 Ohm @ 1.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Series	-
Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C2.9A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 50μAGate Charge (Qg) (Max) @ Vgs17nC @ 10VInput Capacitance (Ciss) (Max) @ Vds440pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)96W (Tc)Rds On (Max) @ Id, Vgs4.5 Ohm @ 1.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature For Capacitance Supplier Device Package Package / Case 2.9A (Tc) 4.5V @ 50μA 4.5V @ 50μA 4.5V @ 50μA 4.40pF @ 25V 4.5 Ohm @ 1.2A, 10V -55°C ~ 150°C (TJ) Through Hole Supplier Device Package I-Pak TO-251-3 Short Leads, IPak, TO-251AA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 50μAGate Charge (Qg) (Max) @ Vgs17nC @ 10VInput Capacitance (Ciss) (Max) @ Vds440pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)96W (Tc)Rds On (Max) @ Id, Vgs4.5 Ohm @ 1.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Drain to Source Voltage (Vdss)	800V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 4.5 V @ 50μA 17nC @ 10V 440pF @ 25V 440pF @ 25V 450V 440pF @ 25V 450V 450V 450V 450V Through Hole 1-2A, 10V 1-25°C ~ 150°C (TJ) Through Hole 1-Pak TO-251-3 Short Leads, IPak, TO-251AA	Current - Continuous Drain (Id) @ 25°C	2.9A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 440pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 Ohm @ 1.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 440pF @ 25V Vgs (Max) ET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 Ohm @ 1.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs(th) (Max) @ Id	4.5V @ 50μA
Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 96W (Tc) Rds On (Max) @ Id, Vgs 4.5 Ohm @ 1.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Gate Charge (Qg) (Max) @ Vgs	17nC @ 10V
FET Feature - Power Dissipation (Max) 96W (Tc) Rds On (Max) @ Id, Vgs 4.5 Ohm @ 1.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Input Capacitance (Ciss) (Max) @ Vds	440pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 Ohm @ 1.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs4.5 Ohm @ 1.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Power Dissipation (Max)	96W (Tc)
Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Rds On (Max) @ Id, Vgs	4.5 Ohm @ 1.2A, 10V
Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Mounting Type	Through Hole
	Supplier Device Package	I-Pak
Report errors?	Package / Case	TO-251-3 Short Leads, IPak, TO-251AA
		Report errors?

NDD03N80Z-1G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

NDD03N80Z-1G Payment Methods





















NDD03N80Z-1G Shipping Methods













If you have any question about NDD03N80Z-1G, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com